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Electronic supplementary information

Strongly Adhering ZnO Crystal Layer via Seed/buffer-free, Low-Temperature Direct Growth on a Polyimide Film Using Solution Process

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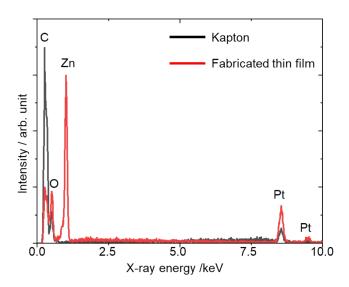


Figure S1. Surficial EDS spectra of Kapton and the fabricated product.